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## Logic level TOPFET SMD version of BUK117-50DL

#### **Product specification**

# BUK128-50DL

## DESCRIPTION

Monolithic temperature and overload protected logic level power MOSFET in TOPFET2 technology assembled in a 3 pin surface mount plastic package.

## **APPLICATIONS**

General purpose switch for driving

- lamps
- . motors
- solenoids
- heaters

in automotive systems and other applications.

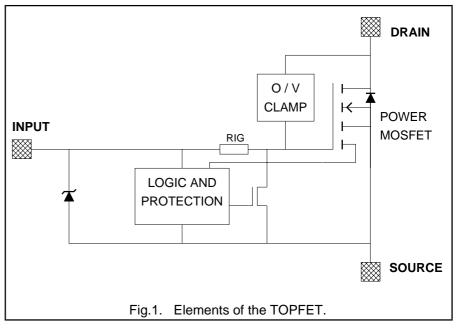
## **FEATURES**

- TrenchMOS output stage
- Current limiting
- Overload protection
- .
- Overtemperature protection Protection latched reset by input
- 5 V logic compatible input level Control of output stage and .
- supply of overload protection circuits derived from input Low operating input current permits direct drive by
- micro-controller
- ESD protection on all pins
- Overvoltage clamping for turn off of inductive loads

# QUICK REFERENCE DATA

| SYMBOL   | PARAMETER   |   | MAX.                               | UNIT                          |
|--|---|---|------------------------------------|-------------------------------|
| $V_{DS} \\ I_D \\ P_D \\ T_j \\ R_{DS(ON)} \\ I_{ISL}$ | Continuous drain source voltag<br>Continuous drain current<br>Total power dissipation<br>Continuous junction temperatur<br>Drain-source on-state resistanc<br>Input supply current V <sub>1</sub> | e | 50<br>8<br>40<br>150<br>100<br>650 | V<br>A<br>W<br>°C<br>mΩ<br>μA |

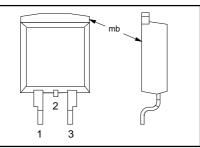
## FUNCTIONAL BLOCK DIAGRAM



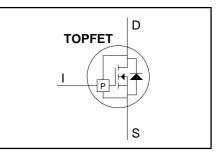
#### **PINNING - SOT404**

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | input       |
| 2   | drain       |
| 3   | source      |
| mb  | drain       |

#### **PIN CONFIGURATION**



## SYMBOL



## Logic level TOPFET SMD version of BUK117-50DL

## BUK128-50DL

#### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

| SYMBOL           | PARAMETER                                    | CONDITIONS                                       | MIN. | MAX.    | UNIT |
|------------------|--|--|------|---------|------|
| V <sub>DS</sub>  | Continuous drain source voltage <sup>1</sup> | -  | -    | 50      | V    |
| I <sub>D</sub>   | Continuous drain current                     | $V_{IS} = 5 V; T_{mb} = 25 °C$                   | -    | self -  | А    |
|                  |  |  |      | limited |      |
| I <sub>D</sub>   | Continuous drain current                     | V <sub>IS</sub> = 5 V; T <sub>mb</sub> ≤110 °C   | -    | 8       | A    |
| I,               | Continuous input current                     | -  | -5   | 5       | mA   |
| I <sub>IRM</sub> | Non-repetitive peak input current            | t <sub>p</sub> ≤ 1 ms                            | -10  | 10      | mA   |
| P <sub>D</sub>   | Total power dissipation                      | t <sub>p</sub> ≤ 1 ms<br>T <sub>mb</sub> ≤ 25 °C | -    | 40      | W    |
| T <sub>stg</sub> | Storage temperature                          | -  | -55  | 175     | °C   |
| T                | Continuous junction temperature <sup>2</sup> | normal operation                                 | -    | 150     | °C   |
| $T_{sold}$       | Case temperature                             | during soldering                                 | -    | 260     | °C   |

#### ESD LIMITING VALUE

| SYMBOL         | PARAMETER                                 | CONDITIONS  |   | MAX. | UNIT |
|----------------|---|---|---|------|------|
| V <sub>c</sub> | Electrostatic discharge capacitor voltage | Human body model;<br>C = 250 pF; R = 1.5 k $\Omega$ | - | 2    | kV   |

#### **OVERVOLTAGE CLAMPING LIMITING VALUES**

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

| SYMBOL                               | PARAMETER   | CONDITIONS  | MIN. | MAX.      | UNIT     |
|--------------------------------------|---|---|------|-----------|----------|
| E <sub>DSM</sub><br>E <sub>DRM</sub> | Inductive load turn-off<br>Non-repetitive clamping energy<br>Repetitive clamping energy | $\begin{split} I_{DM} &= 8 \text{ A}; \text{ V}_{DD} \leq 20 \text{ V} \\ T_{mb} \leq 25 \text{ °C} \\ T_{mb} \leq 95 \text{ °C}; \text{ f} = 250 \text{ Hz} \end{split}$ | -    | 100<br>20 | mJ<br>mJ |

## **OVERLOAD PROTECTION LIMITING VALUE**

With an adequate protection supply provided via the input pin, TOPFET can protect itself from two types of overload - overtemperature and short circuit load.

| SYMBOL          | PARAMETER                         | REQUIRED CONDITION           | MIN. | MAX. | UNIT |
|-----------------|-----------------------------------|------------------------------|------|------|------|
| V <sub>DS</sub> | Drain source voltage <sup>3</sup> | $4~V \leq V_{IS} \leq 5.5~V$ | 0    | 35   | V    |

## THERMAL CHARACTERISTIC

| SYMBOL               | PARAMETER                                       | CONDITIONS                | MIN. | TYP. | MAX. | UNIT |
|----------------------|---|---------------------------|------|------|------|------|
| R <sub>th j-mb</sub> | Thermal resistance<br>Junction to mounting base | -                         | -    | 2.5  | 3.1  | K/W  |
| R <sub>th j-a</sub>  | Junction to ambient                             | minimum footprint FR4 PCB | -    | 50   | -    | K/W  |

<sup>1</sup> Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.

 $<sup>\</sup>mathbf{2}$  A higher  $T_j$  is allowed as an overload condition but at the threshold  $T_{j(TO)}$  the over temperature trip operates to protect the switch.

<sup>3</sup> All control logic and protection functions are disabled during conduction of the source drain diode.

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## **OUTPUT CHARACTERISTICS**

Limits are for -40°C  $\leq$  T<sub>mb</sub>  $\leq$  150°C; typicals are for T<sub>mb</sub> = 25 °C unless otherwise specified

| SYMBOL               | PARAMETER                     | CONDITIONS  | MIN. | TYP. | MAX. | UNIT |
|----------------------|-------------------------------|---|------|------|------|------|
|                      | Off-state                     | $V_{IS} = 0 V$  |      |      |      |      |
| V <sub>(CL)DSS</sub> | Drain-source clamping voltage | I <sub>D</sub> = 10 mA  | 50   | -    | -    | V    |
|                      |                               | $I_{\text{DM}}=1 \text{ A};  t_{\text{p}} \leq 300 \; \mu\text{s};  \delta \leq 0.01$ | 50   | 60   | 70   | V    |
| I <sub>DSS</sub>     | Drain source leakage current  | $V_{DS} = 40 V$   | -    | -    | 100  | μA   |
|                      |                               | T <sub>mb</sub> = 25 °C   | -    | 0.1  | 10   | μΑ   |
|                      | On-state                      | $I_{\text{DM}}$ = 3 A; $t_{\text{p}}$ $\leq$ 300 $\mu s;$ $\delta$ $\leq$ 0.01        |      |      |      |      |
| R <sub>DS(ON)</sub>  | Drain-source resistance       | $V_{IS} \ge 4.4 V$  | -    | -    | 190  | mΩ   |
| - ( - )              |                               | T <sub>mb</sub> = 25 °C   | -    | 68   | 100  | mΩ   |
|                      |                               | $V_{IS} \ge 4 V$  | -    | -    | 200  | mΩ   |
|                      |                               | T <sub>mb</sub> = 25 °C   | -    | 72   | 105  | mΩ   |

#### **OVERLOAD CHARACTERISTICS**

 $\underline{-40^{\circ}C} \leq T_{mb} \leq 150^{\circ}C \text{ unless otherwise specified.}$ 

| SYMBOL                                 | PARAMETER  | CONDITIONS   | MIN.      | TYP.      | MAX.      | UNIT    |
|--|--|--|-----------|-----------|-----------|---------|
| I <sub>D</sub>                         | Short circuit load<br>Drain current limiting                                 | $V_{DS} = 13 V$<br>$V_{IS} = 5 V;$<br>$4.4 V \le V_{IS} \le 5.5 V$<br>$T_{mb} = 25^{\circ}C$                           | 8<br>6    | 12<br>-   | 16<br>18  | AA      |
|  |  | $4 \text{ V} \leq V_{\text{IS}} \leq 5.5 \text{ V}$  | 5         | -         | 18        | A       |
| P <sub>D(TO)</sub><br>T <sub>DSC</sub> | Overload protection<br>Overload power threshold<br>Characteristic time       | $V_{IS} = 5 V;$ $T_{mb} = 25^{\circ}C$<br>device trips if $P_D > P_{D(TO)}$<br>which determines trip time <sup>1</sup> | 20<br>200 | 55<br>350 | 80<br>600 | W<br>μs |
| T <sub>j(TO)</sub>                     | Overtemperature protection<br>Threshold junction<br>temperature <sup>2</sup> |  | 150       | 170       | -         | °C      |

<sup>1</sup> Trip time  $t_{d sc}$  varies with overload dissipation  $P_D$  according to the formula  $t_{d sc} \approx T_{DSC} / ln[P_D / P_{D(TO)}]$ .

**<sup>2</sup>** This is independent of the dV/dt of input voltage  $V_{IS}$ .

## **INPUT CHARACTERISTICS**

The supply for the logic and overload protection is taken from the input. Limits are for -40°C  $\leq$  T<sub>mb</sub>  $\leq$  150°C; typicals are for T<sub>mb</sub> = 25°C unless otherwise specified

| SYMBOL              | PARAMETER   | CONDITIONS                       |                                  | MIN.       | TYP.       | MAX.       | UNIT     |
|---------------------|---|----------------------------------|----------------------------------|------------|------------|------------|----------|
| $V_{\text{IS(TO)}}$ | Input threshold voltage   | $V_{DS} = 5 V; I_{D} = 1 mA$     | T <sub>mb</sub> = 25°C           | 0.6<br>1.1 | -<br>1.6   | 2.4<br>2.1 | V<br>V   |
| I <sub>IS</sub>     | Input supply current  | normal operation;                | $V_{IS} = 5 V$<br>$V_{IS} = 4 V$ | 100<br>80  | 220<br>195 | 400<br>330 | μΑ<br>μΑ |
| I <sub>ISL</sub>    | Input supply current  | protection latched;              | $V_{IS} = 5 V$<br>$V_{IS} = 3 V$ | 200<br>130 | 400<br>250 | 650<br>430 | μΑ<br>μΑ |
| V <sub>ISR</sub>    | Protection reset voltage <sup>1</sup>                           | reset time $t_r \ge 100 \ \mu s$ |                                  | 1.5        | 2          | 2.9        | V        |
| t <sub>ir</sub>     | Latch reset time  | $V_{IS1} = 5 V, V_{IS2} < 1 V$   |                                  | 10         | 40         | 100        | μs       |
| $V_{(CL)IS}$        | Input clamping voltage  | l <sub>1</sub> = 1.5 mA          |                                  | 5.5        | -          | 8.5        | V        |
| R <sub>IG</sub>     | Input series resistance <sup>2</sup><br>to gate of power MOSFET |                                  | $T_{mb} = 25^{\circ}C$           | -          | 33         | -          | kΩ       |

#### SWITCHING CHARACTERISTICS

 $T_{mb}$  = 25 °C;  $V_{DD}$  = 13 V; resistive load  $R_L$  = 4  $\Omega$ . Refer to waveform figure and test circuit.

| SYMBOL             | PARAMETER           | CONDITIONS     | MIN. | TYP. | MAX. | UNIT |
|--------------------|---------------------|----------------|------|------|------|------|
| t <sub>d on</sub>  | Turn-on delay time  | $V_{IS} = 5 V$ | -    | 8    | 20   | μs   |
| t <sub>r</sub>     | Rise time           |                | -    | 20   | 50   | μs   |
| t <sub>d off</sub> | Turn-off delay time | $V_{IS} = 0 V$ | -    | 25   | 70   | μs   |
| t <sub>f</sub>     | Fall time           |                | -    | 16   | 40   | μs   |

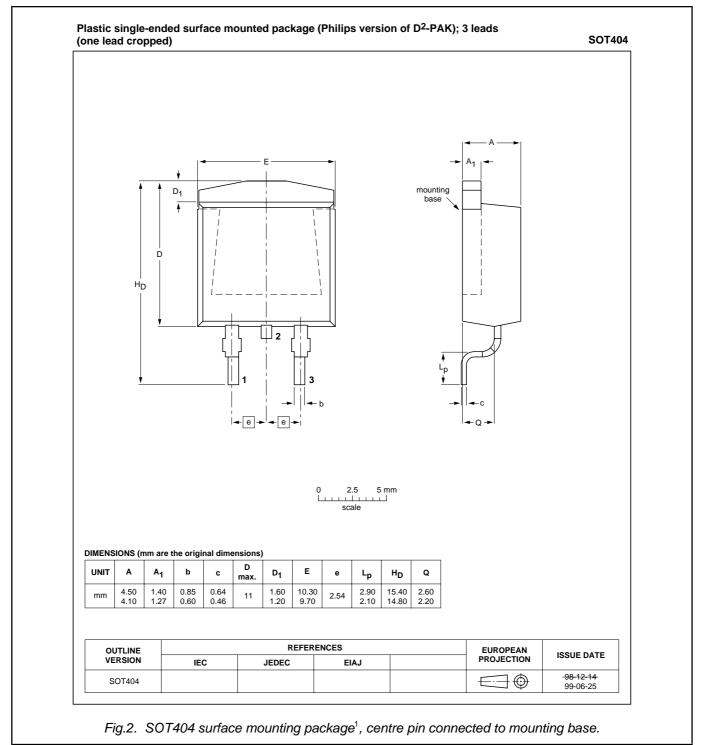
<sup>1</sup> The input voltage below which the overload protection circuits will be reset.

<sup>2</sup> Not directly measureable from device terminals.

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#### MECHANICAL DATA



<sup>1</sup> Epoxy meets UL94 V0 at 1/8". Net mass: 1.4 g For soldering guidelines and SMD footprint design, please refer to Data Handbook SC18.

## Logic level TOPFET SMD version of BUK117-50DL

## BUK128-50DL

#### DEFINITIONS

| DATA SHEET STA                    | TUS                            |   |
|-----------------------------------|--------------------------------|---|
| DATA SHEET<br>STATUS <sup>1</sup> | PRODUCT<br>STATUS <sup>2</sup> | DEFINITIONS   |
| Objective data                    | Development                    | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice  |
| Preliminary data                  | Qualification                  | This data sheet contains data from the preliminary specification.<br>Supplementary data will be published at a later date. Philips<br>Semiconductors reserves the right to change the specification without<br>notice, in ordere to improve the design and supply the best possible<br>product                                    |
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#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

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